

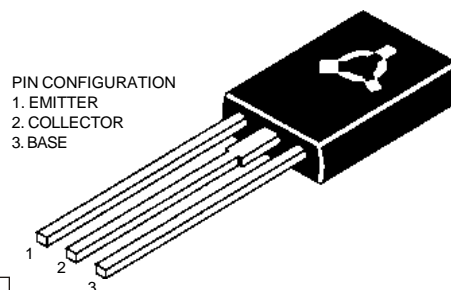
**TO-126 (SOT-32) Plastic Package**

**CSC1162**

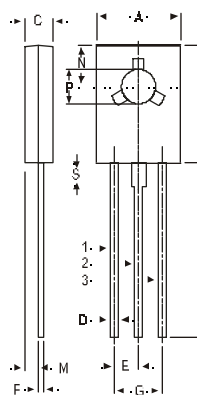
**CSC1162 NPN PLASTIC POWER TRANSISTOR**

Complementary CSA715

Low frequency Power Amplifier



**PIN CONFIGURATION**  
 1. EMITTER  
 2. COLLECTOR  
 3. BASE



DIM	MIN.	MAX.
A	7.4	7.8
B	10.5	10.8
C	2.4	2.7
D	0.7	0.9
E	2.25 TYP.	
F	0.49	0.75
G	4.5 TYP.	
L	15.7 TYP.	
M	1.27 TYP.	
N	3.75 TYP.	
P	3.0	3.2
S	2.5 TYP.	

ALL DIMENSIONS IN MM

**ABSOLUTE MAXIMUM RATINGS**

Collector-base voltage (open emitter)	$V_{CBO}$	max.	35 V
Collector-emitter voltage (open base)	$V_{CEO}$	max.	35 V
Collector current	$I_C$	max.	2.5 A
Total power dissipation up to $T_C = 25^\circ C$	$P_{tot}$	max.	10 W
Junction temperature	$T_j$	max.	150 $^\circ C$
Collector-emitter saturation voltage $I_C = 2A; I_B = 0.2A$	$V_{CEsat}$	max.	1.0 V
D.C. current gain $I_C = 0.5A; V_{CE} = 2V$	$h_{FE}$	min.	60
		max.	320

**RATINGS** (at  $T_A=25^\circ C$  unless otherwise specified)

Limiting values			
Collector-base voltage (open emitter)	$V_{CBO}$	max.	35 V
Collector-emitter voltage (open base)	$V_{CEO}$	max.	35 V

## CSC1162

Emitter-base voltage (open collector)	$V_{EBO}$	max.	5.0 V
Collector current	$I_C$	max.	2.5 A
Collector current (Peak)	$I_C$	max.	3.0 A
Total power dissipation up to $T_A = 25\text{ }^\circ\text{C}$	$P_{tot}$	max.	0.75 W
Total power dissipation up to $T_C = 25\text{ }^\circ\text{C}$	$P_{tot}$	max.	10 W
Junction temperature	$T_j$	max.	150 $^\circ\text{C}$
Storage temperature	$T_{stg}$		65 to +150 $^\circ\text{C}$

### CHARACTERISTICS

$T_{amb} = 25\text{ }^\circ\text{C}$  unless otherwise specified

Collector cutoff current $I_E = 0; V_{CB} = 35\text{V}$	$I_{CBO}$	max.	20 $\mu\text{A}$
Breakdown voltages $I_C = 10\text{ mA}; I_B = 0$	$V_{CEO}$	min.	35 V
$I_C = 1\text{ mA}; I_E = 0$	$V_{CBO}$	min.	35 V
$I_E = 1\text{ mA}; I_C = 0$	$V_{EBO}$	min.	5 V
Saturation voltage $I_C = 2\text{ A}; I_B = 0.2\text{ A}$	$V_{CEsat}^*$	max.	1.0 V
Base-emitter on voltage $I_C = 1.5\text{A}; V_{CE} = 2\text{V}$ (Pulse)	$V_{BE(on)}$	max.	1.5 V
D.C. current gain $I_C = 0.5\text{ A}; V_{CE} = 2\text{ V}^{**}$	$h_{FE}$	min.	60
		max.	320
$I_C = 1.5\text{ A}; V_{CE} = 2\text{ V}$ (Pulse)	$h_{FE}$	min.	20
Transition frequency $I_C = 0.2\text{ A}; V_{CE} = 2\text{ V}$	$f_T$	typ.	180 MHz

**\*\*  $h_{FE}$  classification: B: 60-120 C: 100-200 D: 160-320**

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**Continental Device India Limited**

C-120 Naraina Industrial Area, New Delhi 110 028, India.  
Telephone + 91-11-2579 6150, 5141 1112 Fax + 91-11-2579 5290, 5141 1119  
email@cdil.com www.cdilsemi.com